LX23T7P20
P-channel Enhancement Mode Power MOSFET

Features

- -20V, -7A
  $R_{DS(ON)}$<32mΩ @ V_{GS} = -4.5V
  $R_{DS(ON)}$<40mΩ @ V_{GS} = -2.5V
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

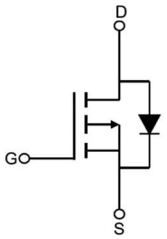
Application

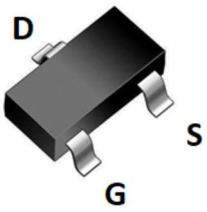
- Load Switch
- PWM Application
- Power management

Marking

- Marking : P72

SOT-23





Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25℃	-7	A
		T_A = 100℃	-4.6	A
I_{DM}	Pulsed Drain Current note1		-28	A
P_D	Power Dissipation	T_A = 25℃	2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		62.5	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -20V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-0.4	-	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}= -4.5V, I_D= -7A	-	-	32	mΩ
		V_{GS}= -2.5V, I_D= -5A	-	-	40	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -10V, V_{GS}=0V, f=1.0MHz	-	2000	-	pF
C_{oss}	Output Capacitance		-	242	-	pF
C_{rss}	Reverse Transfer Capacitance		-	231	-	pF
Q_g	Total Gate Charge	V_{DS}= -10V, I_D= -3A, V_{GS}= -4.5V	-	15.3	-	nC
Q_{gs}	Gate-Source Charge		-	2.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	4.4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -10V, I_D= -7A, V_{GS}= -4.5V, R_{GEN}=2.5Ω	-	10	-	ns
t_r	Turn-on Rise Time		-	31	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	28	-	ns
t_f	Turn-off Fall Time		-	8	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-7	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-28	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -5A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

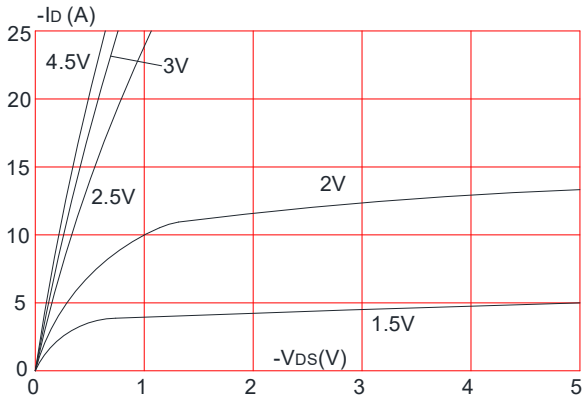


Figure 2: Typical Transfer Characteristics

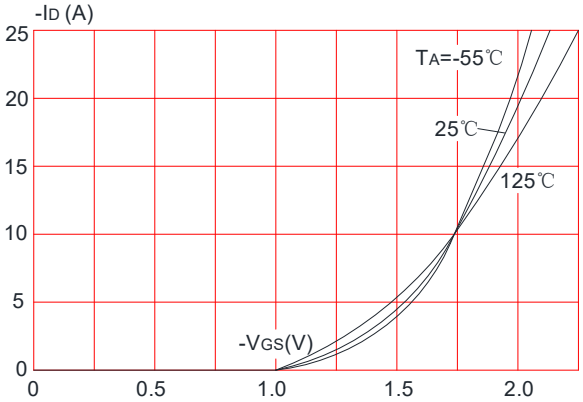


Figure 3: On-resistance vs. Drain Current

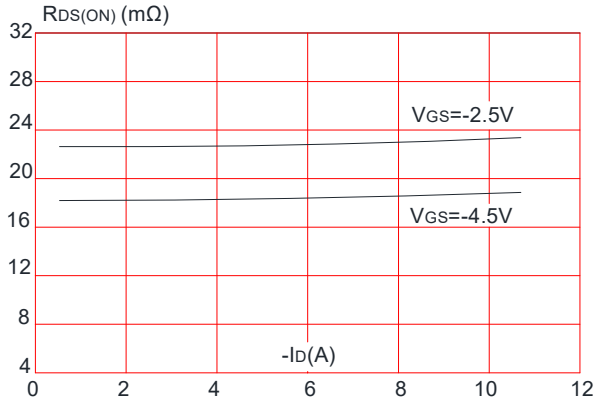


Figure 4: Body Diode Characteristics

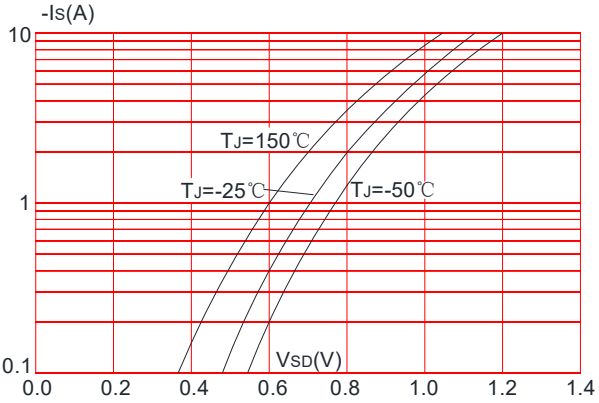


Figure 5: Gate Charge Characteristics

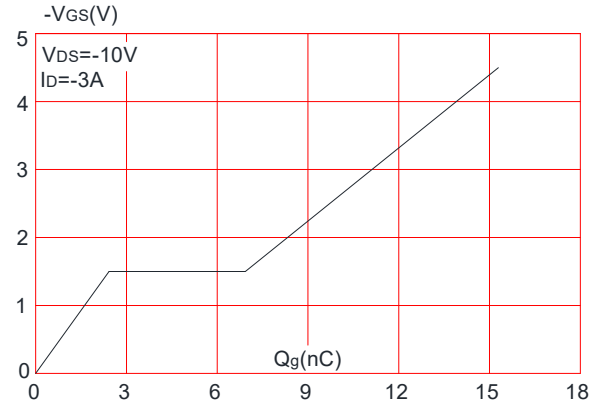


Figure 6: Capacitance Characteristics

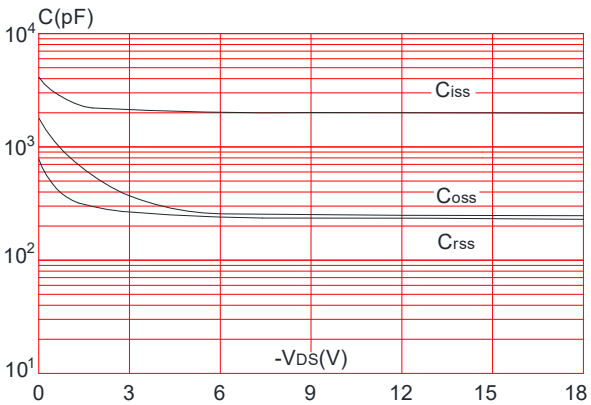


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

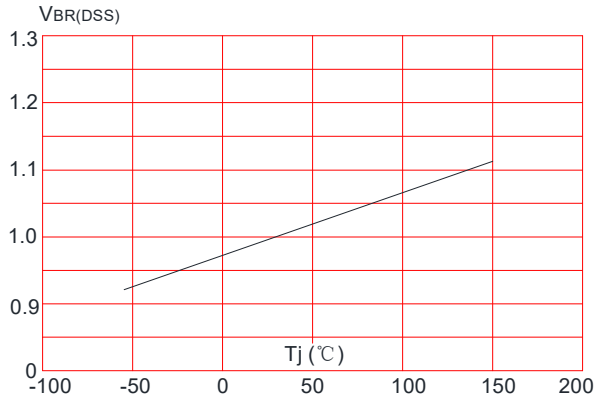


Figure 8: Normalized on Resistance vs. Junction Temperature

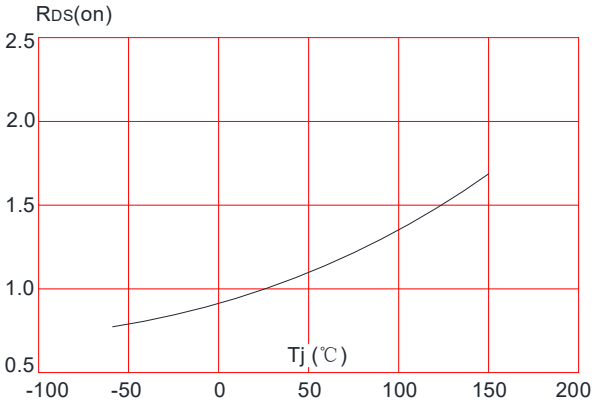


Figure 9: Maximum Safe Operating Area

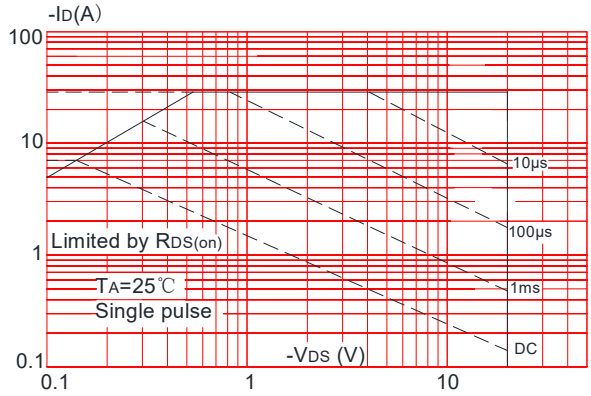


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

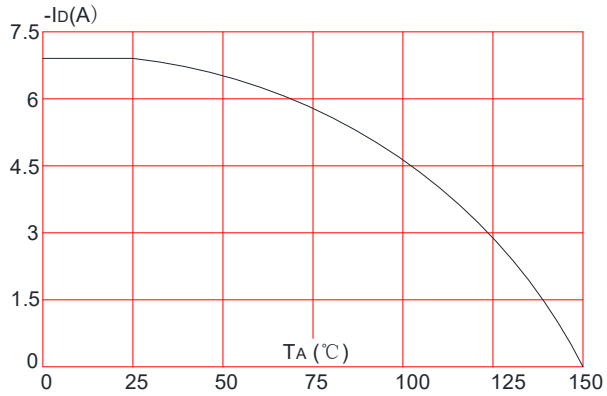
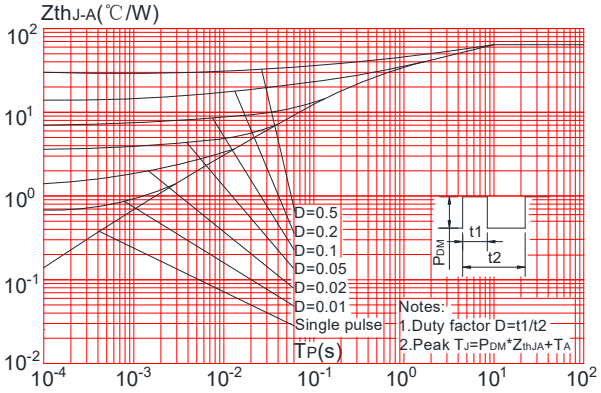
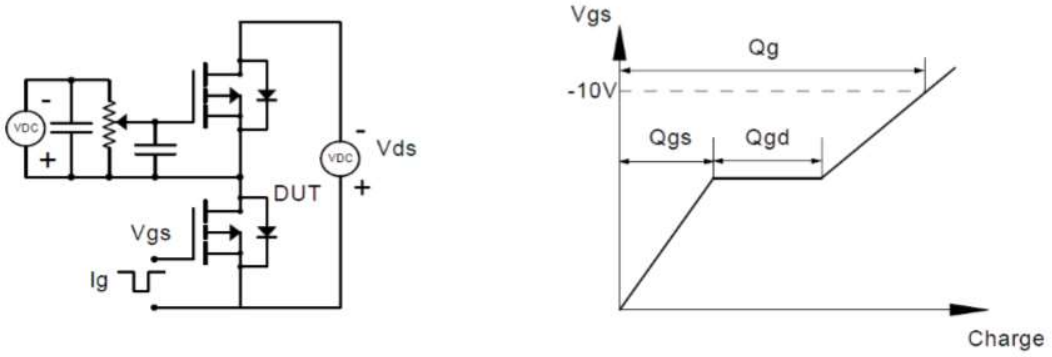


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

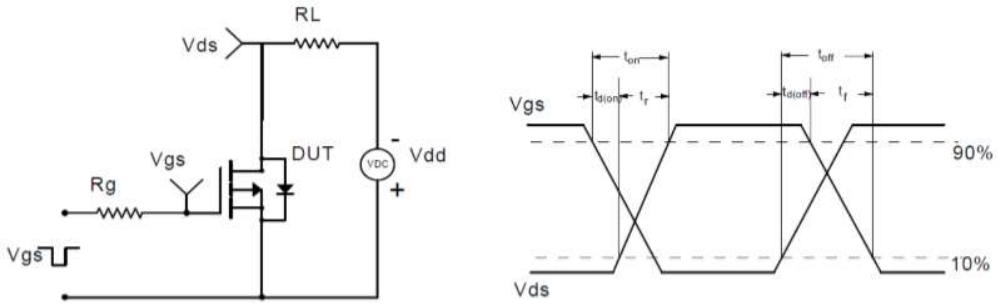


Test Circuit

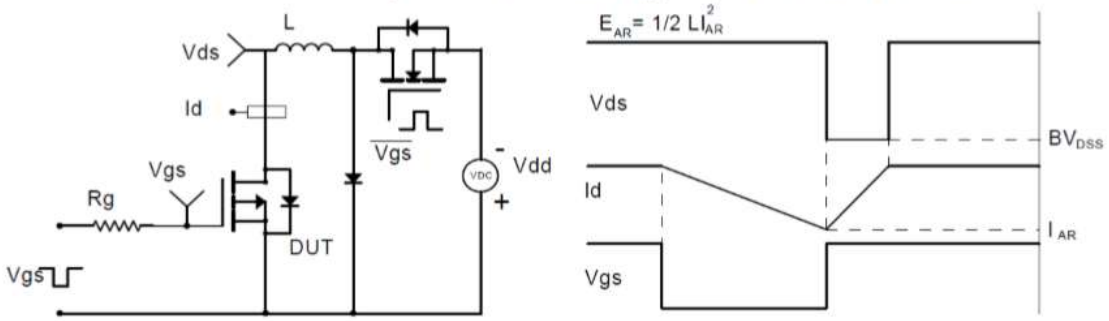
Gate Charge Test Circuit & Waveform



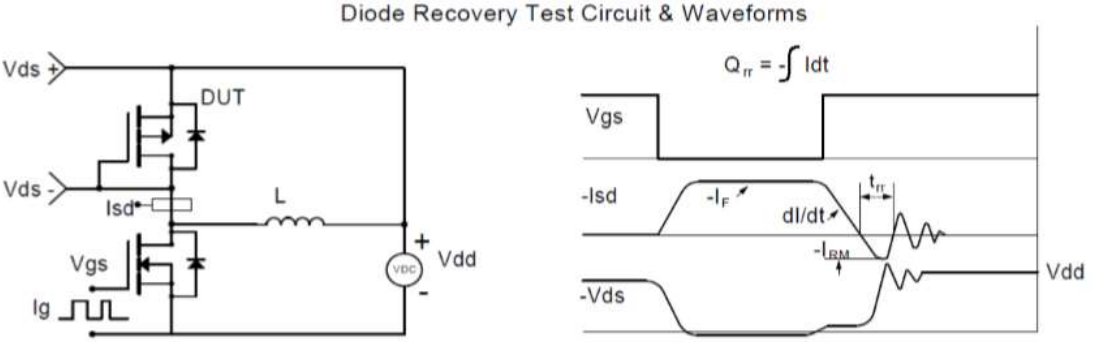
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

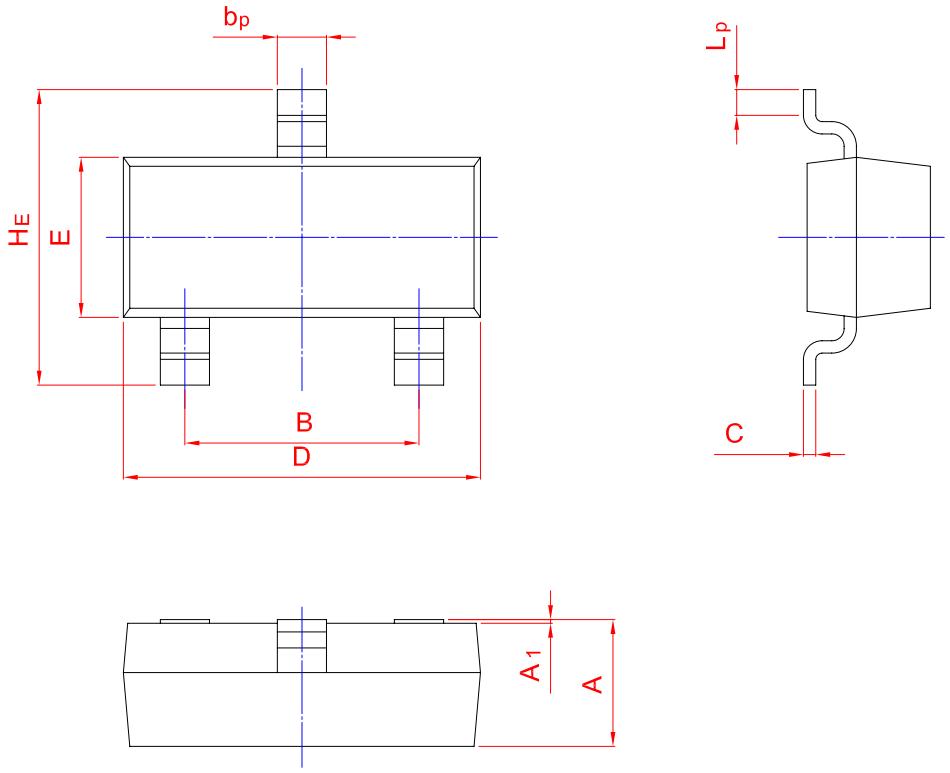


Diode Recovery Test Circuit & Waveforms



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20